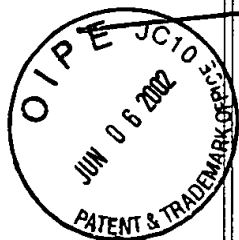


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In re Appln. Of: ITO  
Serial No.: 09/735,005  
Filed: December 12, 2000  
For: SEMICONDUCTOR DEVICE HAVING DUMMY GATES...  
Group: 2811  
Examiner: TRAN, THIEN F. DOCKET: NEC 444

6P 2811  
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JUN 11 2002  
TECHNOLOGY CENTER  
#8/22/02  
Suresh

Assistant Commissioner of Patents and Trademarks  
Washington, D.C. 20231

AMENDMENT **B4**

Dear Sir:

This Amendment is being filed in response to the Official Action mailed March 8, 2002.

Please amend the Application as follows:

IN THE SPECIFICATION:

Please replace the paragraph beginning at page 2, line 6, with the following rewritten paragraph:

a1  
In the second prior art method, however, when designing a photomask for the dummy gate, additional design time for dummy patterns thereof is required. In particular, if a plurality of kinds of comb-shaped gate patterns are present, the additional design time is enormously large, which would increase the turnaround time, thus increasing the manufacturing cost.

Please replace the paragraph beginning at page 6, line 3, with the following rewritten paragraph:

a2  
In the semiconductor device of Figs. 3A, 3B and 3C manufactured by the photomask of Fig. 4, however, when designing the photomask of Fig. 4, an additional design time for the dummy patterns DP is required. In particular, if a plurality of kinds of comb-shaped gate

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